

Dual P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
-30	0.025 @ $V_{GS} = -10$ V	-9.4
	0.030 @ $V_{GS} = -4.5$ V	-8.6
	0.045 @ $V_{GS} = -2.5$ V	-7.0

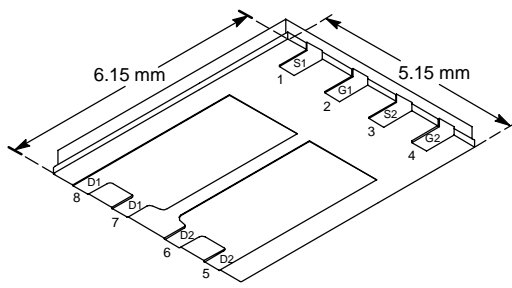
FEATURES

- TrenchFET® Power MOSFET
- New Low Thermal Resistance PowerPAK™ Package with Low 1.07-mm Profile

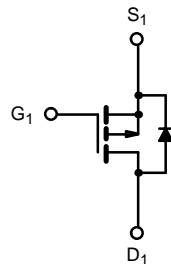
APPLICATIONS

- 1–2 Cell Li-Ion Battery Switch
- Bus Load Switch for Notebook/Desktop Computers

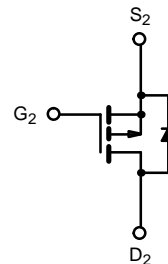
PowerPAK™ SO-8



Bottom View



P-Channel MOSFET



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)					
Parameter		Symbol	10 secs	Steady State	Unit
Drain-Source Voltage		V_{DS}	-30		V
Gate-Source Voltage		V_{GS}	± 12		
Continuous Drain Current ($T_J = 150^\circ\text{C}$) ^a	$T_A = 25^\circ\text{C}$	I_D	-9.4	-6.0	A
	$T_A = 70^\circ\text{C}$		-7.5	-4.8	
Pulsed Drain Current		I_{DM}	-30		
continuous Source Current (Diode Conduction) ^a		I_S	-2.9	-1.2	
Maximum Power Dissipation ^a	$T_A = 25^\circ\text{C}$	P_D	3.5	1.4	W
	$T_A = 70^\circ\text{C}$		2.2	0.9	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150		$^\circ\text{C}$

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	$t \leq 10$ sec	R_{thJA}	26	35	$^\circ\text{C/W}$
	Steady State		60	85	
Maximum Junction-to-Case (Drain)		R_{thJC}	2.2	2.7	

Notes

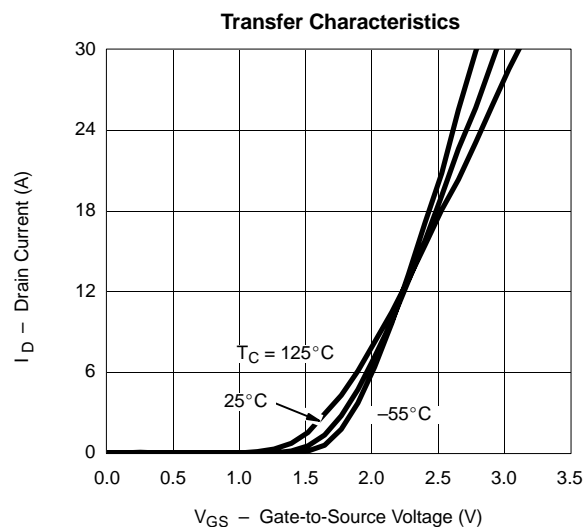
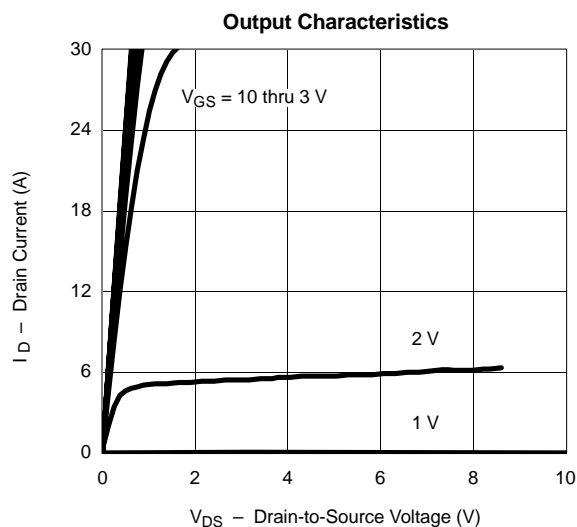
a. Surface Mounted on 1" x 1" FR4 Board.

SPECIFICATIONS (T_J = 25 °C UNLESS OTHERWISE NOTED)

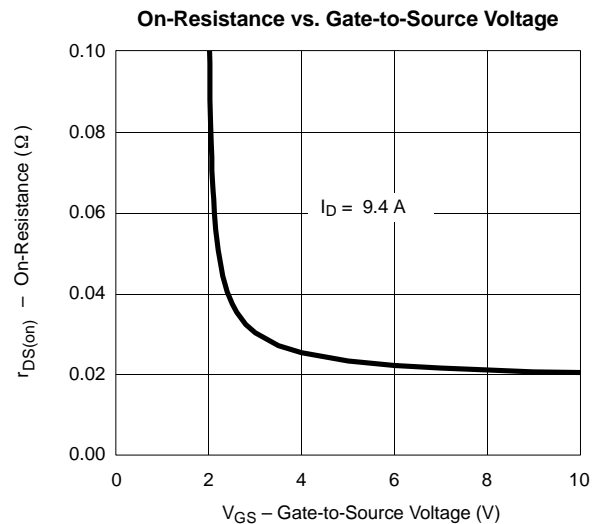
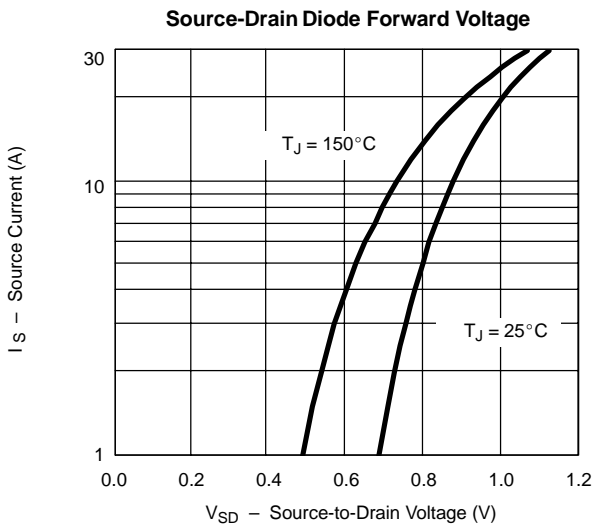
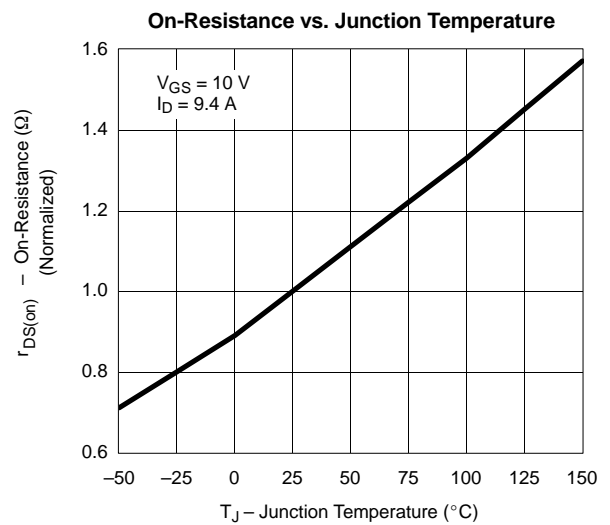
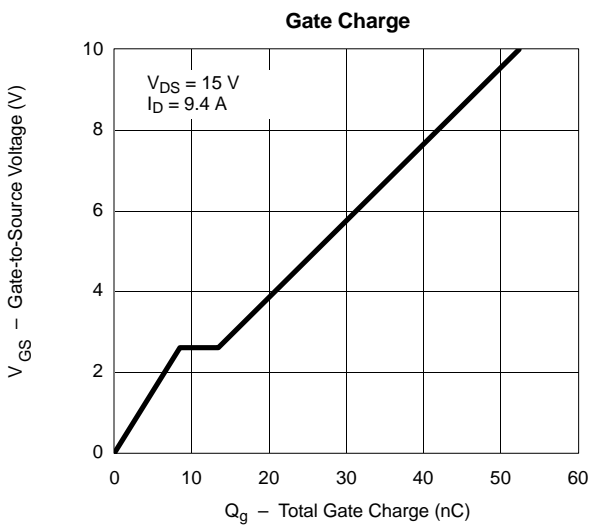
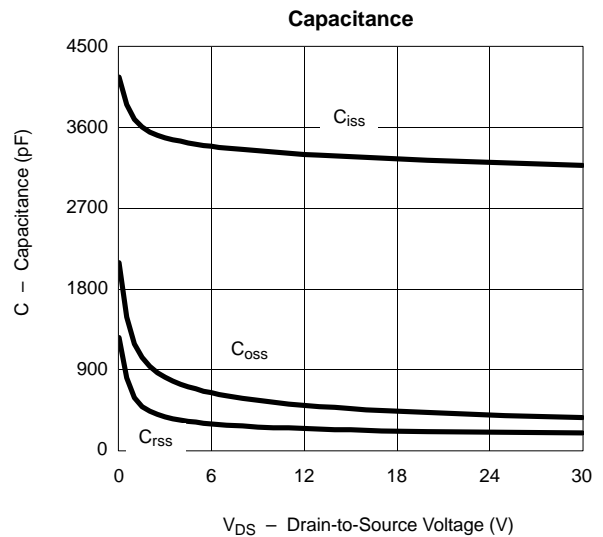
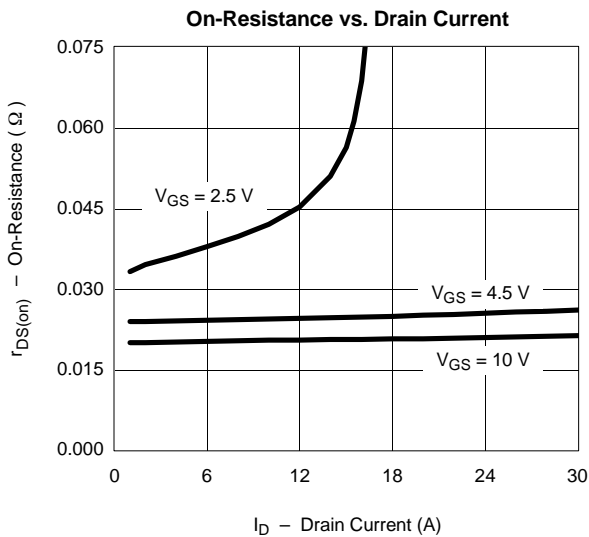
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250 μA	-0.60			V
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±12 V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -24 V, V _{GS} = 0 V			-1	μA
		V _{DS} = -24 V, V _{GS} = 0 V, T _J = 55 °C			-5	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≤ -5 V, V _{GS} = -10 V	-30			A
Drain-Source On-State Resistance ^a	r _{DS(on)}	V _{GS} = -10 V, I _D = -9.4 A		0.020	0.025	Ω
		V _{GS} = -4.5 V, I _D = -8.6 A		0.024	0.030	
		V _{GS} = -2.5 V, I _D = -3.0 A		0.037	0.045	
Forward Transconductance ^a	g _{fs}	V _{DS} = -15 V, I _D = -9.4 A		15		S
Diode Forward Voltage ^a	V _{SD}	I _S = -2.9 A, V _{GS} = 0 V		-0.8	-1.2	V
Dynamic^b						
Total Gate Charge	Q _g	V _{DS} = -15 V, V _{GS} = -4.5 V, I _D = -9.4 A		24	36	nC
Gate-Source Charge	Q _{gs}			8.5		
Gate-Drain Charge	Q _{gd}			5.0		
Gate Resistance	R _G			2.9		Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = -15 V, R _L = 15 Ω I _D ≈ -1 A, V _{GEN} = -10 V, R _G = 6 Ω		18	27	ns
Rise Time	t _r			40	60	
Turn-Off Delay Time	t _{d(off)}			100	150	
Fall Time	t _f			60	90	
Source-Drain Reverse Recovery Time	t _{rr}		I _F = -2.9 A, di/dt = 100 A/μs		50	

Notes

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
b. Guaranteed by design, not subject to production testing.

TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)

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